

DATA SHEET

NE/SA/SE5532/5532A

Internally-compensated dual low noise
operational amplifier

Product data
Supersedes data of 1997 Sep 29

2001 Aug 03

Internally-compensated dual low noise operational amplifier

NE/SA/SE5532/5532A

DESCRIPTION

The 5532 is a dual high-performance low noise operational amplifier. Compared to most of the standard operational amplifiers, such as the 1458, it shows better noise performance, improved output drive capability and considerably higher small-signal and power bandwidths.

This makes the device especially suitable for application in high-quality and professional audio equipment, instrumentation and control circuits, and telephone channel amplifiers. The op amp is internally compensated for gains equal to one. If very low noise is of prime importance, it is recommended that the 5532A version be used because it has guaranteed noise voltage specifications.

FEATURES

- Small-signal bandwidth: 10 MHz
- Output drive capability: 600 Ω , 10 V_{RMS}
- Input noise voltage: 5 nV/ \sqrt{Hz} (typical)
- DC voltage gain: 50000
- AC voltage gain: 2200 at 10 kHz
- Power bandwidth: 140 kHz
- Slew rate: 9 V/ μs
- Large supply voltage range: ± 3 to ± 20 V
- Compensated for unity gain

PIN CONFIGURATIONS

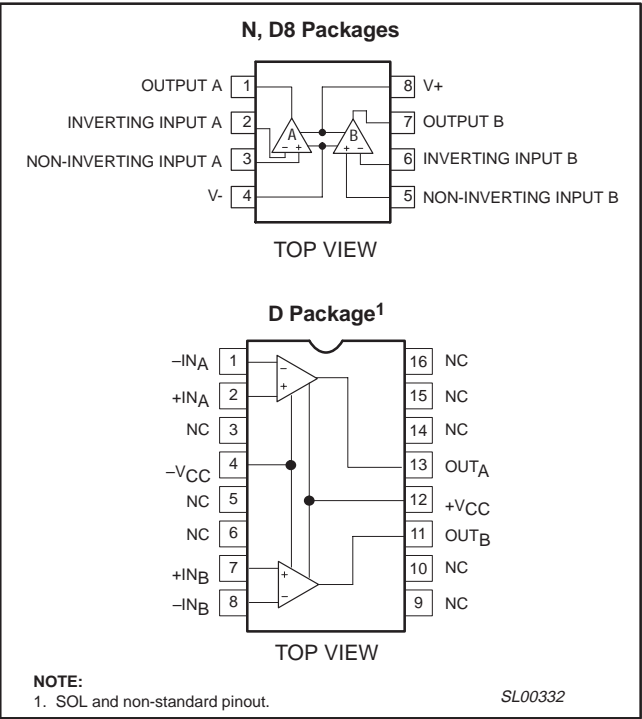


Figure 1. Pin Configurations

ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE	DWG #
8-Pin Small Outline Package (SO)	0 °C to 70 °C	NE5532AD8	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	0 °C to 70 °C	NE5532AN	SOT97-1
16-Pin Plastic Small Outline Large (SOL) Package	0 °C to 70 °C	NE5532D	SOT162-1
8-Pin Small Outline Package (SO)	0 °C to 70 °C	NE5532D8	SOT96-1
8-Pin Plastic Dual In-Line Package (DIP)	0 °C to 70 °C	NE5532N	SOT97-1
8-Pin Plastic Dual In-Line Package (DIP)	-40 °C to +85 °C	SA5532N	SOT97-1
8-Pin Small Outline Package (SO)	-55 °C to +125 °C	SE5532AD8	SOT96-1
16-Pin Plastic Dual In-Line Package (DIP)	-55 °C to +125 °C	SE5532N	SOT38-4

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EQUIVALENT SCHEMATIC (EACH AMPLIFIER)

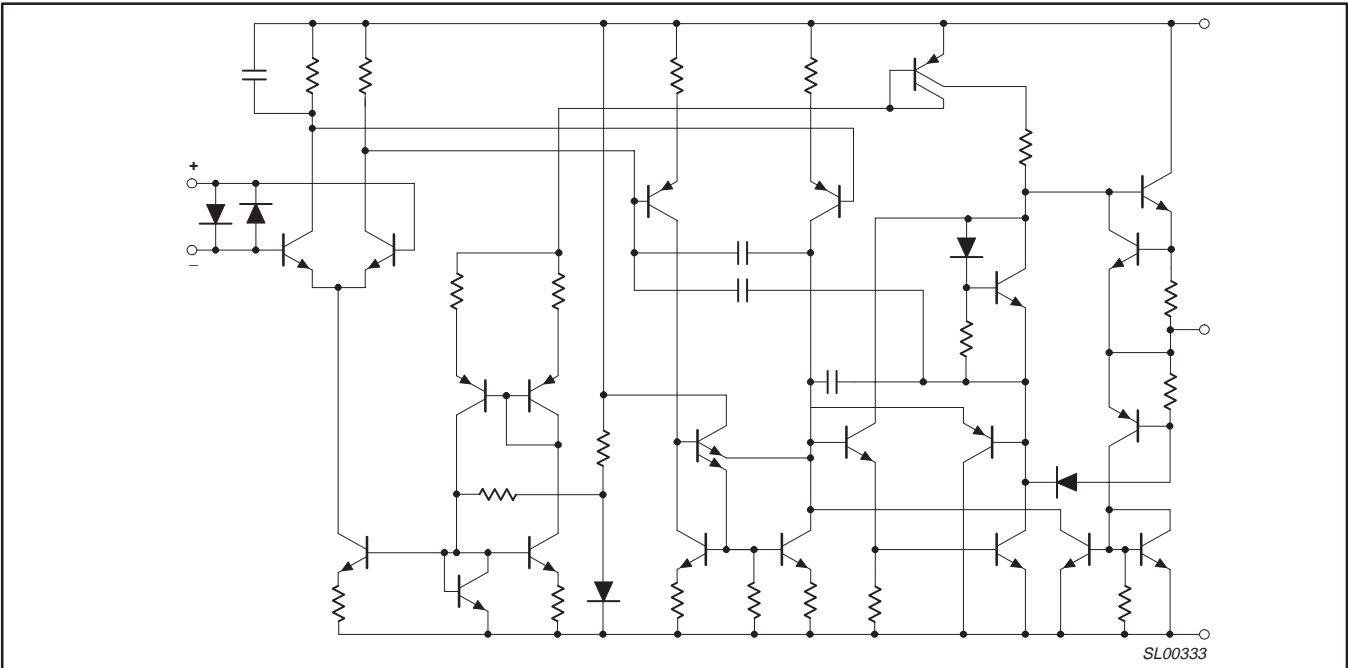


Figure 2. Equivalent Schematic (Each Amplifier)

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_S	Supply voltage	± 22	V
V_{IN}	Input voltage	$\pm V_{SUPPLY}$	V
V_{DIFF}	Differential input voltage ¹	± 0.5	V
T_{amb}	Operating temperature range NE5532/A SA5532 SE5532/A	0 to 70 -40 to +85 -55 to +125	°C °C °C
T_{stg}	Storage temperature	-65 to +150	°C
T_j	Junction temperature	150	°C
P_D	Maximum power dissipation, $T_{amb} = 25\text{ °C}$ (still-air) ² 8 D8 package 8 N package 16 D package	780 1200 1200	mW mW mW
T_{sld}	Lead soldering temperature (10 sec max)	230	°C

NOTES:

- Diodes protect the inputs against over-voltage. Therefore, unless current-limiting resistors are used, large currents will flow if the differential input voltage exceeds 0.6V. Maximum current should be limited to $\pm 10\text{ mA}$.
- Thermal resistances of the above packages are as follows:
N package at 100 °C/W
D package at 105 °C/W
D8 package at 160 °C/W

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DC ELECTRICAL CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_S = \pm 15\text{ V}$, unless otherwise specified. 1, 2, 3

SYMBOL	PARAMETER	TEST CONDITIONS	SE5532/A			NE5532/A, SA5532			UNIT
			Min	Typ	Max	Min	Typ	Max	
V_{OS}	Offset voltage	Over temperature		0.5	2		0.5	4	mV
$\Delta V_{OS}/\Delta T$				5	3		5	5	mV $\mu\text{V}/^{\circ}\text{C}$
I_{OS}	Offset current	Over temperature			100		10	150	nA
$\Delta I_{OS}/\Delta T$				200	200		200	200	nA $\text{pA}/^{\circ}\text{C}$
I_B	Input current	Over temperature		200	400		200	800	nA
$\Delta I_B/\Delta T$				5	700		5	1000	nA $\text{nA}/^{\circ}\text{C}$
I_{CC}	Supply current	Over temperature		8	10.5		8	16	mA
					13				mA
V_{CM}	Common-mode input range		± 12	± 13		± 12	± 13		V
CMRR	Common-mode rejection ratio		80	100		70	100		dB
PSRR	Power supply rejection ratio			10	50		10	100	$\mu\text{V}/\text{V}$
A_{VOL}	Large-signal voltage gain	$R_L \geq 2\text{ k}\Omega$; $V_O = \pm 10\text{ V}$	50	100		25	100		V/mV
		Over temperature	25			15			V/mV
		$R_L \geq 600\text{ }\Omega$; $V_O = \pm 10\text{ V}$	40	50		15	50		V/mV
		Over temperature	20			10			V/mV
V_{OUT}	Output swing	$R_L \geq 600\text{ }\Omega$	± 12	± 13		± 12	± 13		V
		Over temperature	± 10	± 12		± 10	± 12		
		$R_L \geq 600\text{ }\Omega$; $V_S = \pm 18\text{ V}$	± 15	± 16		± 15	± 16		
		Over temperature	± 12	± 14		± 12	± 14		
		$R_L \geq 2\text{ k}\Omega$	± 13	± 13.5		± 13	± 13.5		
		Over temperature	± 12	± 12.5		± 10	± 12.5		
R_{IN}	Input resistance		30	300		30	300		k Ω
I_{SC}	Output short circuit current		10	38	60	10	38	60	mA

NOTES:

- Diodes protect the inputs against overvoltage. Therefore, unless current-limiting resistors are used, large currents will flow if the differential input voltage exceeds 0.6 V. Maximum current should be limited to $\pm 10\text{ mA}$.
- For operation at elevated temperature, derate packages based on the package thermal resistance.
- Output may be shorted to ground at $V_S = \pm 15\text{ V}$, $T_{amb} = 25\text{ }^{\circ}\text{C}$. Temperature and/or supply voltages must be limited to ensure dissipation rating is not exceeded.

AC ELECTRICAL CHARACTERISTICS

 $T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_S = \pm 15\text{ V}$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	NE/SE5532/A, SA5532			UNIT
			Min	Typ	Max	
R_{OUT}	Output resistance	$A_V = 30\text{ dB}$ Closed-loop $f = 10\text{ kHz}$, $R_L = 600\text{ }\Omega$		0.3		Ω
	Overshoot	Voltage-follower $V_{IN} = 100\text{ mV}_{P-P}$ $C_L = 100\text{ pF}$; $R_L = 600\text{ }\Omega$		10		%
A_V	Gain	$f = 10\text{ kHz}$		2.2		V/mV
GBW	Gain bandwidth product	$C_L = 100\text{ pF}$; $R_L = 600\text{ }\Omega$		10		MHz
SR	Slew rate			9		V/ μs
	Power bandwidth	$V_{OUT} = \pm 10\text{ V}$ $V_{OUT} = \pm 14\text{ V}$; $R_L = 600\text{ }\Omega$, $V_{CC} = \pm 18\text{ V}$		140 100		kHz kHz

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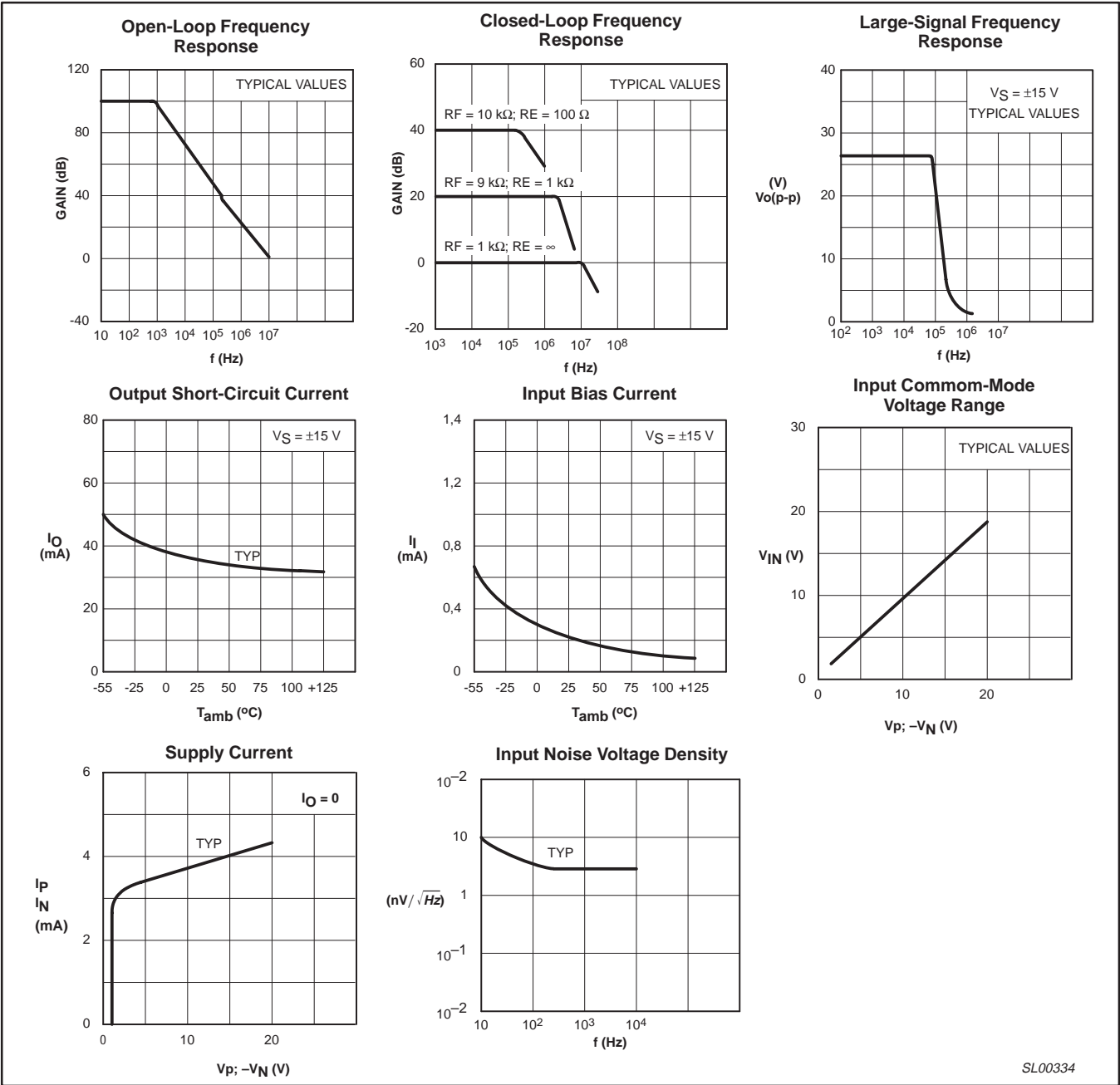
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ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_S = \pm 15\text{ V}$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	NE/SE5532			NE/SA/SE5532A			UNIT
			Min	Typ	Max	Min	Typ	Max	
V_{NOISE}	Input noise voltage	$f_O = 30\text{ Hz}$ $f_O = 1\text{ kHz}$		8 5			8 5	12 6	$\text{nV}/\sqrt{\text{Hz}}$ $\text{nV}/\sqrt{\text{Hz}}$
I_{NOISE}	Input noise current	$f_O = 30\text{ Hz}$ $f_O = 1\text{ kHz}$		2.7 0.7			2.7 0.7		$\text{pA}/\sqrt{\text{Hz}}$ $\text{pA}/\sqrt{\text{Hz}}$
	Channel separation	$f = 1\text{ kHz}$; $R_S = 5\text{ k}\Omega$		110			110		dB

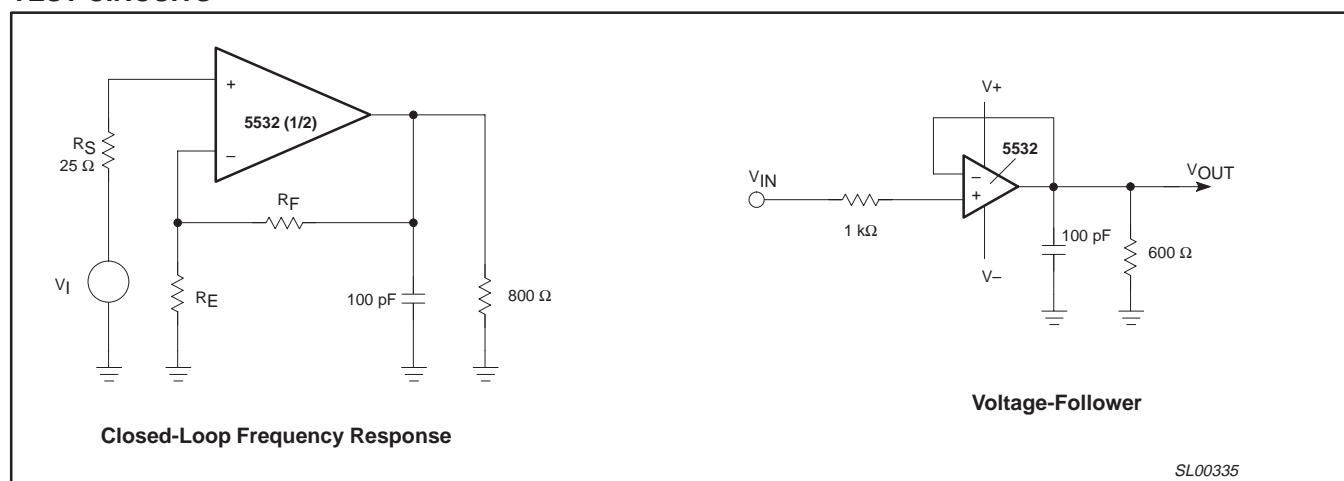
TYPICAL PERFORMANCE CHARACTERISTICS



SL00334

Figure 3. Typical Performance Characteristics

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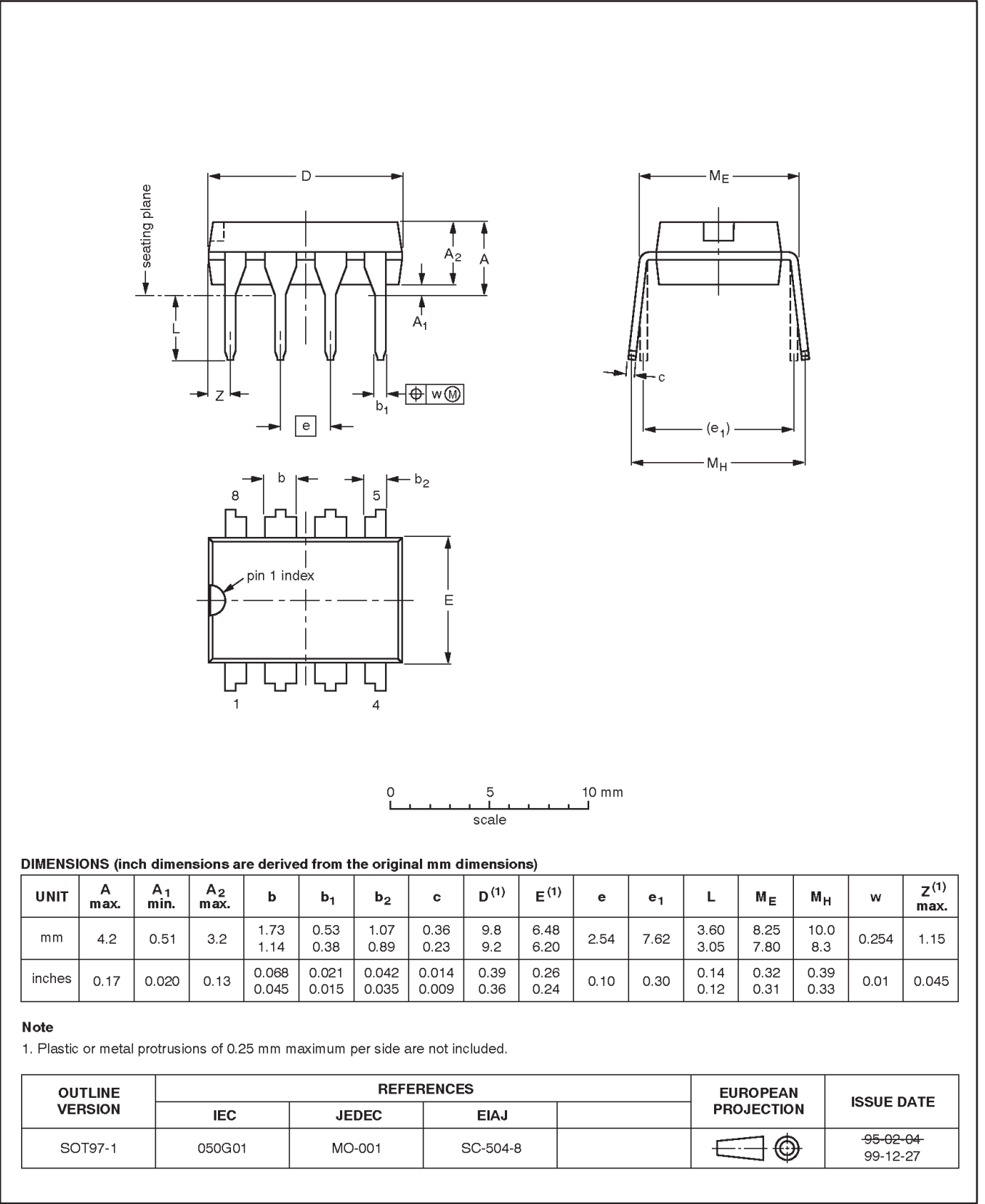
NE/SA/SE5532/5532A**TEST CIRCUITS****Figure 4. Test Circuits**

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DIP8: plastic dual in-line package; 8 leads (300 mil)

SOT97-1

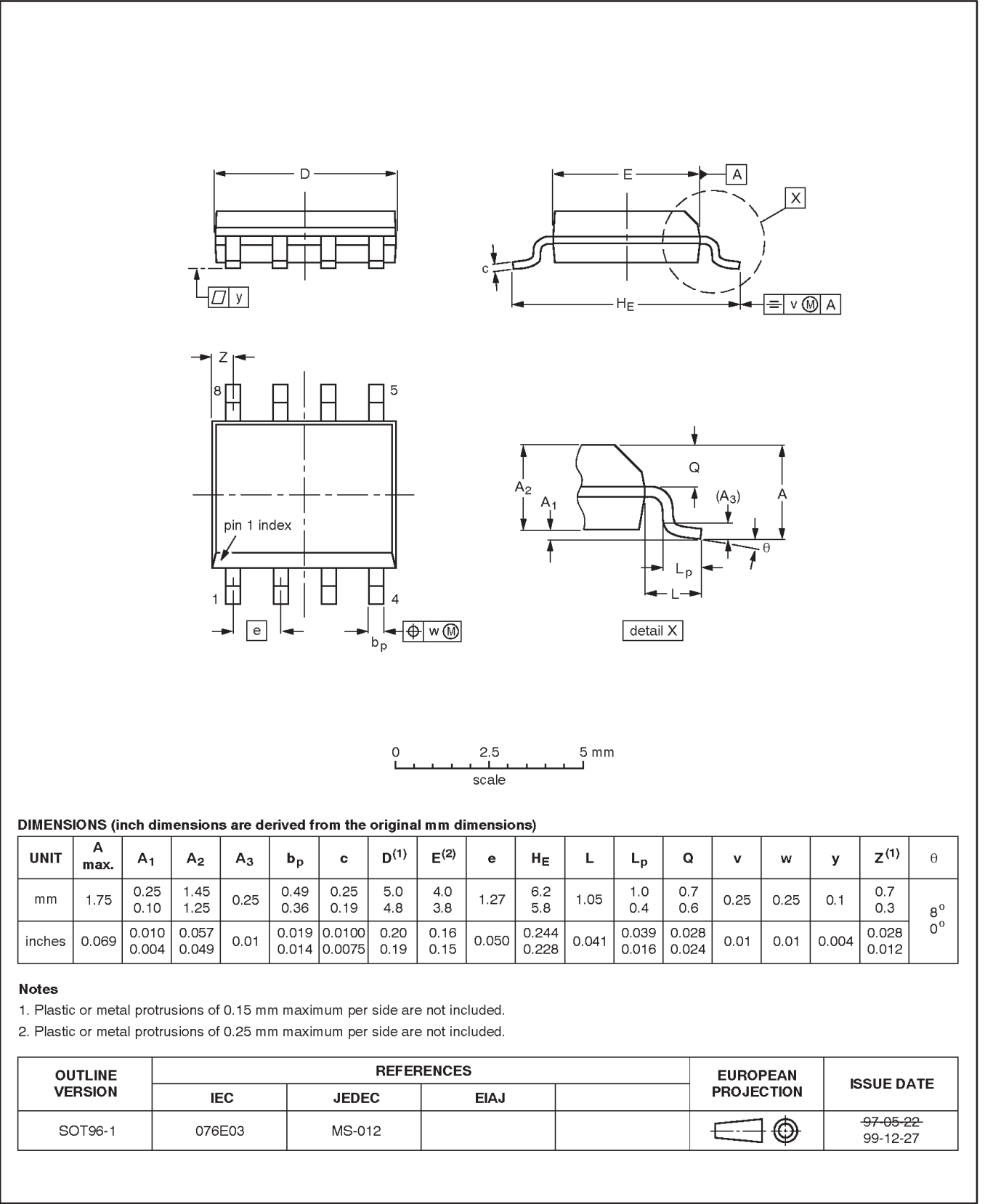


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SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1

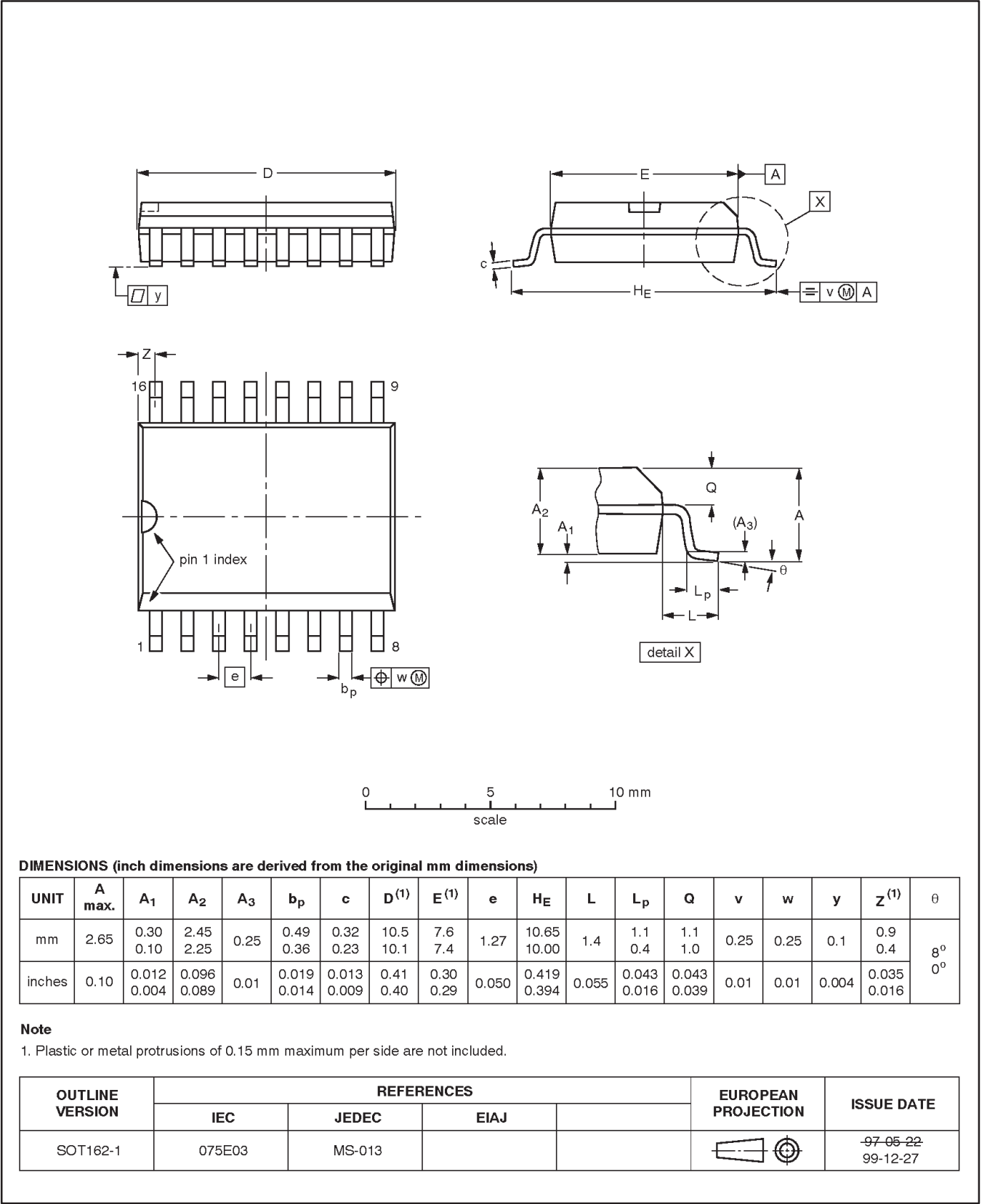


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SO16: plastic small outline package; 16 leads; body width 7.5 mm

SOT162-1

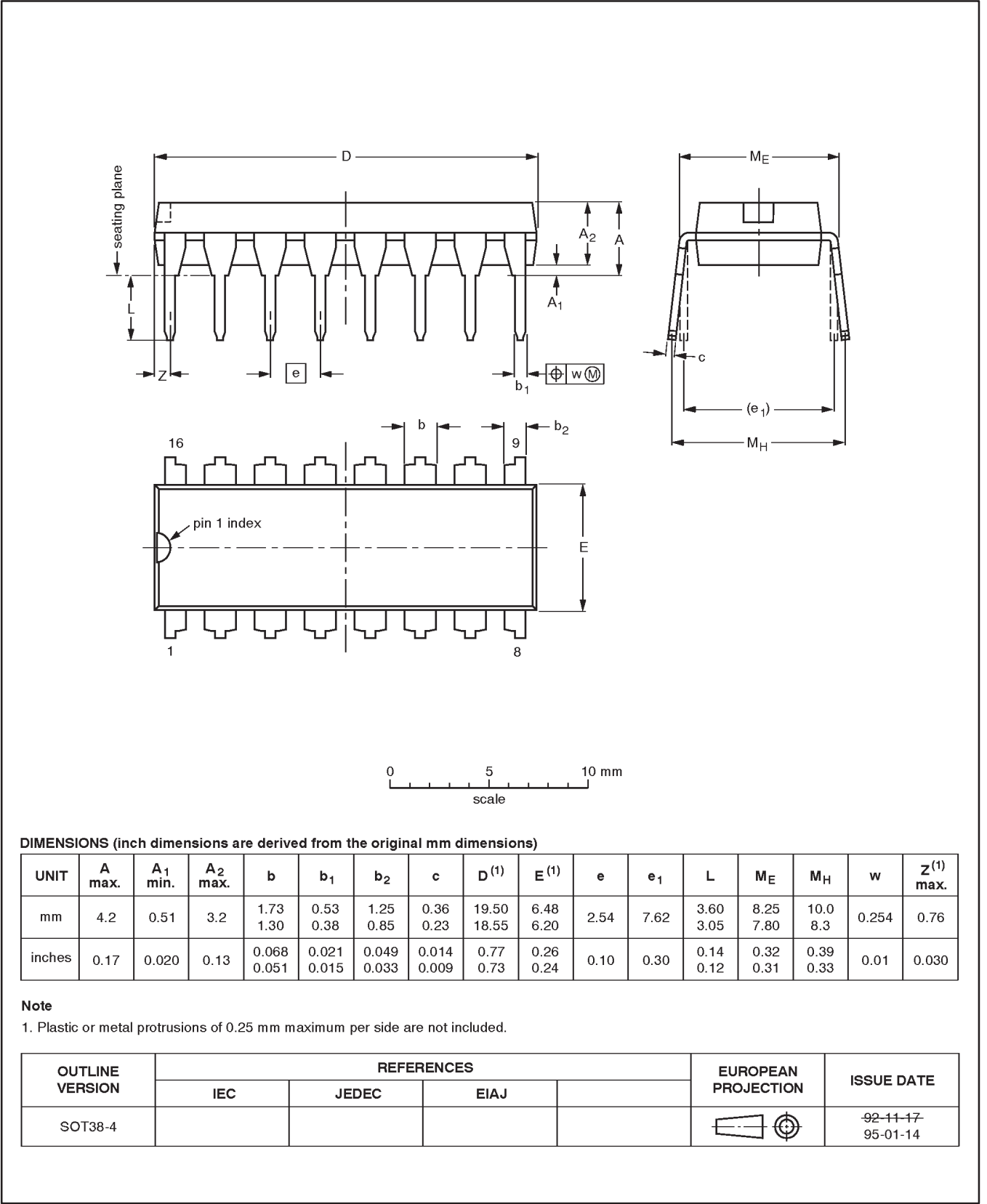


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DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



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NOTES

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Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Date of release: 03-02

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Document order number:

9397 750 09563

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